



Internal Qualification & Reliability Report

DDR3 SDRAM

8Gb – Die Rev. 1
2Gb x 4, 1Gb x 8, 512Mb x 16

CONFIDENTIAL AND PROPRIETARY INFORMATION

IMPORTANT NOTICE

ALLIANCE MAKES NO WARRANTIES, EXPRESSED OR IMPLIED, AS TO THE RELIABILITY TEST RESULTS/ FAILURE RATE ESTIMATES CONTAINED HEREIN, EXCEPT THAT ALLIANCE WARRANTS THAT IT PERFORMED THE RELIABILITY TESTS DESCRIBED HEREIN ACCORDING TO THE SPECIFIED STANDARDS AND THAT THIS REPORT ACCURATELY REFLECTS THE RESULTS OF SUCH TESTS. CUSTOMER EXPRESSLY ACKNOWLEDGES THAT THESE RELIABILITY TEST RESULTS/ FAILURE RATE ESTIMATES ARE ONLY VALID FOR MECHANISMS KNOWN TO BE TEMPERATURE AND/OR VOLTAGE DEPENDENT AND THAT SUCH RELIABILITY TEST RESULTS/ FAILURE RATE ESTIMATES ARE SUBJECT TO OTHER SIGNIFICANT INHERENT LIMITATIONS, INCLUDING BUT NOT LIMITED TO LOW FAILURE COUNTS, TESTING CONDITIONS, ASSUMPTIONS AS TO TYPICAL OPERATING CONDITIONS AND ACCELERATION FACTORS AND LOT-TO-LOT VARIABILITY. CUSTOMER FURTHER ACKNOWLEDGES THAT THESE TESTS WERE CONDUCTED IN SEMICONDUCTOR TEST EQUIPMENT AND NOT IN AN ACTUAL CUSTOMER APPLICATION. THE ACTUAL RELIABILITY RESULTS/FAILURE RATES IN AN ACTUAL APPLICATION MAY MATERIALLY DIFFER DUE TO THE SPECIFIC OPERATING CONDITIONS (INCLUDING BUT NOT LIMITED TO TEMPERATURE AND VOLTAGE), HANDLING AND STORAGE OF THE PRODUCTS, INSTALLATION PROCEDURES, AND THE ACTUAL ENVIRONMENTAL AND ELECTRICAL CONDITIONS THE PRODUCT IS SUBJECT TO IN THE APPLICATION. TO DETERMINE PRODUCT RELIABILITY/FAILURE RATES IN A SPECIFIC APPLICATION, RELIABILITY TESTING MUST BE PERFORMED IN SUCH APPLICATION AS PART OF THE INTERNAL QUALIFICATION OF THE PRODUCT.

ALLIANCE'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER OR PRESIDENT OF ALLIANCE.

EXCEPT AS EXPRESSLY PROVIDED HEREIN, ALLIANCE MAKES NO WARRANTIES, EXPRESSED OR IMPLIED, INCLUDING, BUT NOT LIMITED TO, ANY WARRANTY OF NONINFRINGEMENT, ANY WARRANTY OF MERCHANTABILITY OR WARRANTY OF FITNESS FOR A PARTICULAR PURPOSE. NO AGENT, EMPLOYEE OR REPRESENTATIVE OF ALLIANCE HAS ANY AUTHORITY TO BIND ALLIANCE TO ANY AFFIRMATION, REPRESENTATION OR WARRANTY RELATING TO THE PRODUCTS OTHER THAN AS SPECIFICALLY PROVIDED HEREIN AND CUSTOMER ACKNOWLEDGES AND AGREES THAT ANY SUCH PURPORTED WARRANTY, AFFIRMATION OR REPRESENTATION SHALL BE VOID AND OF NO FORCE AND EFFECT.

Table of Contents

Table 1: Die and Process Tests	1
Table 2: Package: 78-ball TFBGA — Assembly Site: Chipmos TW	2
Table 3: Package: 96-ball TFBGA — Assembly Site: Chipmos TW	3

Qualification Results

Qualification Results — 8Gb DDR3 SDRAM

Table 1: Die and Process Tests

	Test Procedure / Conditions	Test Method Referenced	Duration or Level	Results		Notes
				# Lots	Failed / Tested	
Reliability Level Tests	HIGH TEMPERATURE OPERATING LIFE <i>Stress Conditions:</i> 125°C, 1.3V internal voltage <i>Typical Operating Conditions:</i> 50°C, 1.0V internal voltage at 1.5V external Vdd); 16 FITs Ea=0.5eV; β=7; AF _{OVERALL} =241; Pn=0.916; Device Hrs=2.328 x 10 ⁵	JESD22-A108	168 hrs 504 hrs 1008 hrs	3	0 / 231 0 / 231 0 / 231	1,2
	EARLY LIFE FAILURE RATE <i>Stress Conditions:</i> 125°C, 1.3V internal voltage <i>Typical Operating Conditions:</i> 50°C, 1.0V internal voltage at 1.5V external Vdd); 21 FITs Ea=0.5eV; β=7; AF _{OVERALL} =241; Pn=0.916; Device Hrs=1.797 x 10 ⁵		36 hrs	3	0 / 4993	2
	LOW TEMPERATURE OPERATING LIFE -10°C, 1.3V internal voltage	JESD22-A108	168 hrs 504 hrs 1008 hrs	3	0 / 120 0 / 120 0 / 120	1,2
	HIGH TEMPERATURE STORAGE LIFE 150°C, no bias.	JESD22-A103	504 hrs 1008 hrs	3	0 / 231 0 / 231	1,2
Characterization Tests	ELECTROSTATIC DISCHARGE Human Body Model Charged Device Model	JDS-001 ESDA STM 5.3.1	>2,000V >500V	3 3	0 / 3 0 / 3	1
	LATCH-UP (105°C) I _{Trigger} Overvoltage V _{SUPPLY}	JESD78	>100mA VDD/VDDQ >2.4V	3 3	0 / 6 0 / 6	1
Wafer Level Tests	TIME DEPENDENT DIELECTRIC BREAKDOWN (TDDB)	JESD35A, JESD35-2, JESD92	>10 years	3	Pass	
	ELECTROMIGRATION (EM)	JESD63, JESD61A, JESD202A, JESD87	>10 years	3	Pass	
	CHANNEL HOT CARRIER (CHC)	JESD28, JESD60A	>10 years	3	Pass	
	NEGATIVE BIAS TEMPERATURE INSTABILITY (NBTI)	JESD90	>10 years	3	Pass	

- (1) Alliance primarily references JEDEC standard JESD47 when conducting reliability tests for the qualification of new product. In some tests, other industry standards may be referenced. Note that many tests are carried beyond the minimum recommended by JEDEC. This is to verify that margin exists with respect to intrinsic reliability.
- (2) Preconditioning (without soak): per JEDEC J-STD-020D. Test is performed with 260°C peak reflow.

Qualification Results — 8Gb DDR3 SDRAM (continued)
Table 2: Package: 78-ball TFBGA — Assembly Site: Chipmos TW

	Test Procedure / Conditions	Test Method Referenced	Duration or Level	Results		Notes
				# Lots	Failed / Tested	
Reliability Level Tests	HIGHLY ACCELERATED STRESS TEST 110°C, 85% RH, 1.6V on alternating balls.	JESD22-A110	264 hrs	3	0 / 231	1,2
	TEMPERATURE CYCLE -55°C for 15 min., + 125°C for 15 min., air to air.	JESD22-A104	500 cycles 750 cycles 1000 cycles	3	0 / 231 0 / 231 0 / 231	1,2
	HIGH TEMPERATURE STORAGE LIFE 150°C, no bias.	JESD22-A103	504 hrs 1008 hrs	3	0 / 231 0 / 231	1,3
Characterization Tests	MOISTURE SENSITIVITY LEVEL Peak Reflow Temp = 260°C	J-STD-020	Level 3	3	Pass	1
	BOND INTEGRITY Wire Bond Shear minimum gmf Wire Bond Pull Strength minimum gmf	JESD22-B116 Internal Alliance specs		3 3	12.6 gmf 3.0 gmf	1,4
	SOLDER BALL SHEAR 240°C peak reflow temperature, 1x reflow, minimum gmf	JESD22-B117		3	619 gmf	1

- (1) Alliance primarily references JEDEC standard JESD47 when conducting reliability tests for the qualification of new product. In some tests, other industry standards may be referenced. Note that many tests are carried beyond the minimum recommended by JEDEC. This is to verify that margin exists with respect to intrinsic reliability.
- (2) Preconditioning (with soak): per JEDEC J-STD-020D at rated moisture sensitivity level. Test is performed with 260°C peak reflow.
- (3) Preconditioning (without soak): per JEDEC J-STD-020D. Test is performed with 260°C peak reflow.
- (4) Data leveraged from similar package.

Qualification Results — 8Gb DDR3 SDRAM (continued)
Table 3: Package: 96-ball TFBGA — Assembly Site: Chipmos TW

	Test Procedure / Conditions	Test Method Referenced	Duration or Level	Results		Notes
				# Lots	Failed / Tested	
Reliability Level Tests	HIGHLY ACCELERATED STRESS TEST 110°C, 85% RH, 1.6V on alternating balls.	JESD22-A110	264 hrs	3	0 / 231	1,2
	TEMPERATURE CYCLE -55°C for 15 min., + 125°C for 15 min., air to air.	JESD22-A104	500 cycles 750 cycles 1000 cycles	3	0 / 231 0 / 231 0 / 231	1,2
	HIGH TEMPERATURE STORAGE LIFE 150°C, no bias.	JESD22-A103	504 hrs 1008 hrs	3	0 / 231 0 / 231	1,3,4
Characterization Tests	MOISTURE SENSITIVITY LEVEL Peak Reflow Temp = 260°C	J-STD-020	Level 3	3	Pass	1
	BOND INTEGRITY Wire Bond Shear minimum gmf Wire Bond Pull Strength minimum gmf	JESD22-B116 Internal Alliance specs		3 3	12.6 gmf 3.0 gmf	1
	SOLDER BALL SHEAR 240°C peak reflow temperature, 1x reflow, minimum gmf	JESD22-B117		3	571 gmf	1

- (1) Alliance primarily references JEDEC standard JESD47 when conducting reliability tests for the qualification of new product. In some tests, other industry standards may be referenced. Note that many tests are carried beyond the minimum recommended by JEDEC. This is to verify that margin exists with respect to intrinsic reliability.
- (2) Preconditioning (with soak): per JEDEC J-STD-020D at rated moisture sensitivity level. Test is performed with 260°C peak reflow.
- (3) Preconditioning (without soak): per JEDEC J-STD-020D. Test is performed with 260°C peak reflow.
- (4) Data leveraged from similar package.